

A cross-sectional view of a semiconductor device 30. The device consists of a substrate 31 with a central region 32 and two side regions 33. A layer 34 is formed on the substrate 31. A layer 35 is formed on the side regions 33. A layer 36 is formed on the central region 32. A layer 37 is formed on the side regions 33. A layer 38 is formed on the central region 32. A layer 39 is formed on the central region 32. A layer 40 is formed on the side regions 33. A layer 41 is formed on the central region 32.

FIG.2A

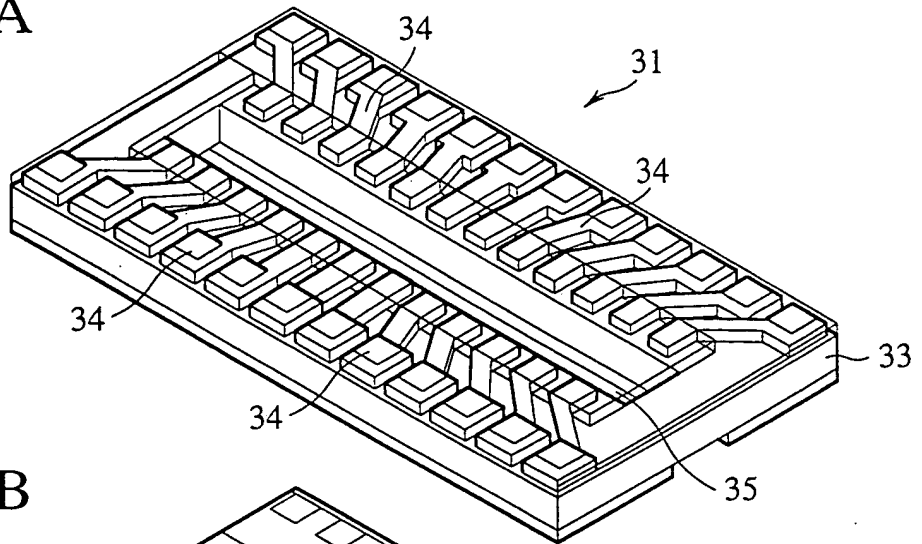


FIG.2B

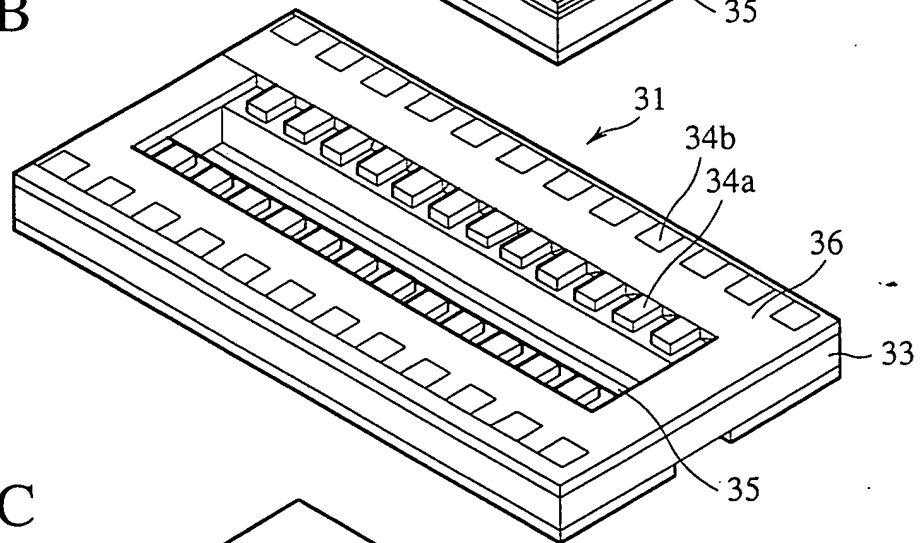
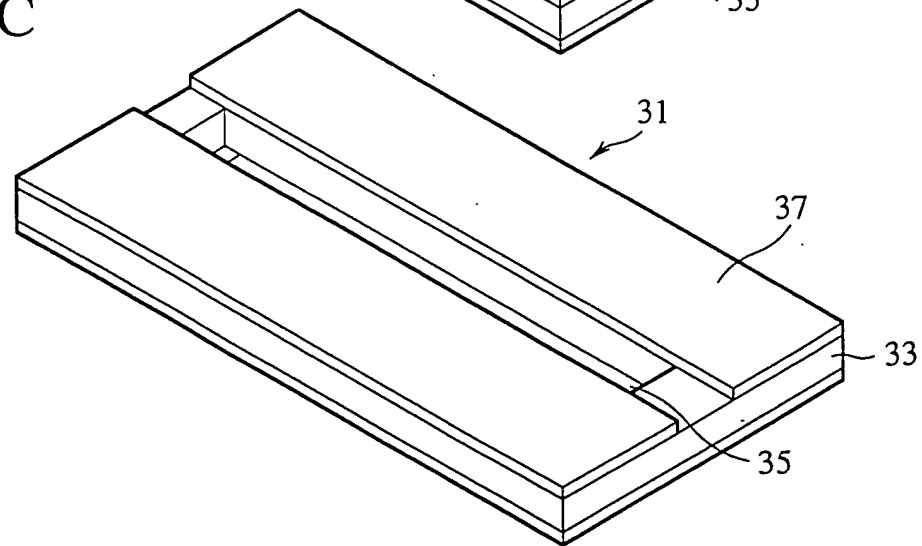


FIG.2C



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FIG.5

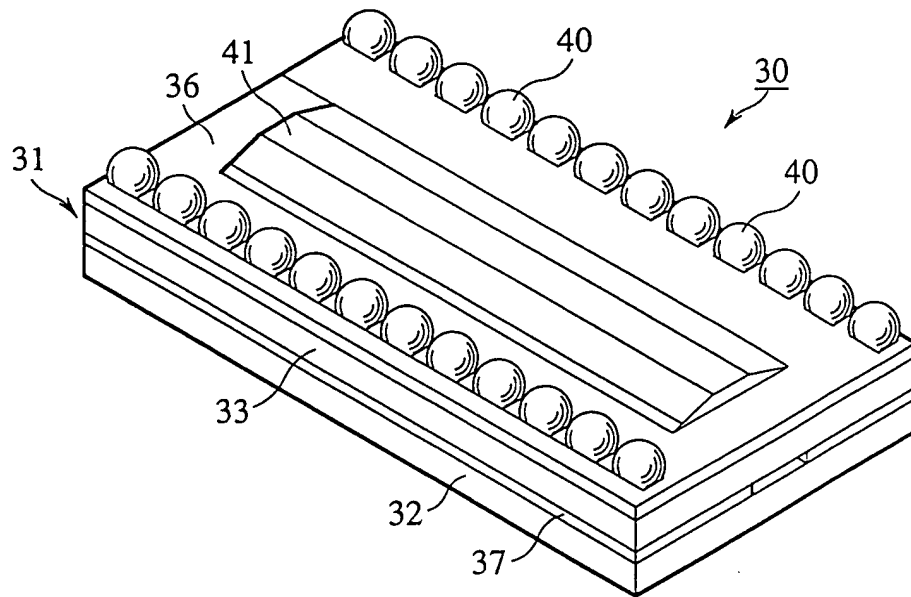


FIG.6

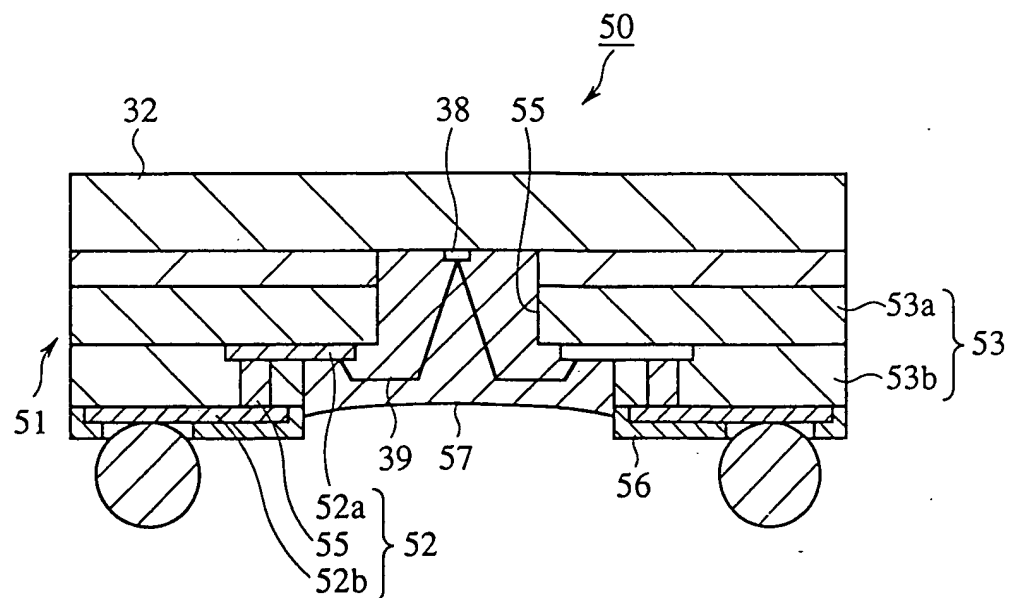


FIG.8

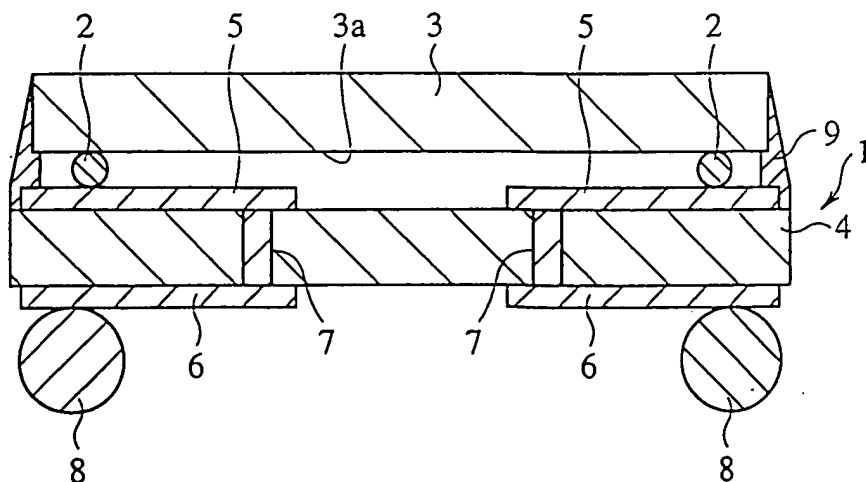


FIG.9

